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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTC115E series NPN resistor-equipped transistors; R1 = 100 kΩ, R2 = 100 kΩ

Product data sheet Supersedes data of 2004 Apr 06 2004 Aug 06



NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	20	mA
R1	bias resistor	100	_	kΩ
R2	bias resistor	100	_	kΩ

DESCRIPTION

NPN resistor equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	KAGE	MARKING CODE	PNP COMPLEMENT
ITPE NUMBER	PHILIPS	EIAJ	MARKING CODE	PNP COMPLEMENT
PDTC115EE	SOT416	SC-75	46	PDTA115EE
PDTC115EEF	SOT490	SC-89	49	PDTA115EEF
PDTC115EK	SOT346	SC-59	56	PDTA115EK
PDTC115EM	SOT883	SC-101	DV	PDTA115EM
PDTC115ES	SOT54 (TO-92)	SC-43	TC115E	PDTA115ES
PDTC115ET	SOT23	_	*44 ⁽¹⁾	PDTA115ET
PDTC115EU	SOT323	SC-70	*15 ⁽¹⁾	PDTA115EU

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CYMPOL		PINNING		
ITPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	PINNING DESCRIPTION base collector emitter base emitter collector		
PDTC115ES	1 R1 R2 3 MAM364	1 2 3	collector		
PDTC115EE PDTC115EEF PDTC115EK PDTC115ET PDTC115EU	3 1 R1 R2 2 Top view MDB269	1 2 3	emitter		
PDTC115EM	2 R1 R2 P2 PMC506	1 2 3	base emitter collector		

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

ORDERING INFORMATION

TYPE NUMBER		PACKAGE						
ITPE NUMBER	NAME	DESCRIPTION	VERSION					
PDTC115EE	_	plastic surface mounted package; 3 leads	SOT416					
PDTC115EEF	_	plastic surface mounted package; 3 leads	SOT490					
PDTC115EK	_	plastic surface mounted package; 3 leads	SOT346					
PDTC115EM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm	SOT883					
PDTC115ES	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54					
PDTC115ET	-	plastic surface mounted package; 3 leads	SOT23					
PDTC115EU	-	plastic surface mounted package; 3 leads	SOT323					

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
Io	output current (DC)		_	20	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT883	notes 2 and 3	_	250	mW
	SOT490	notes 1 and 2	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT833	notes 2 and 3	500	K/W
	SOT490	notes 1 and 2	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	_	_	50	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	_	_	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100 \mu A; V_{CE} = 5 V$	_	1.1	0.5	V
V _{i(on)}	input-on voltage	$I_C = 1 \text{ mA}; V_{CE} = 0.3 \text{ V}$	3	1.5	_	V
R1	input resistor		70	100	130	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	_	_	2.5	pF

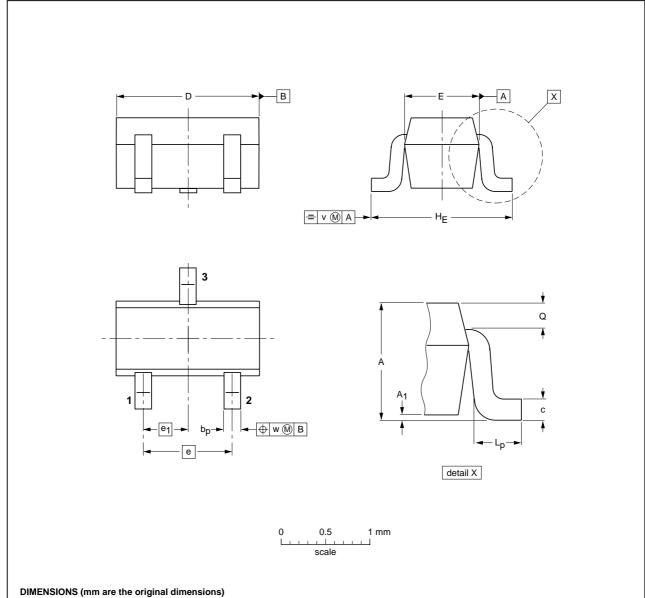
NPN resistor-equipped transistors; $R1 = 100 \text{ k}\Omega$, $R2 = 100 \text{ k}\Omega$

PDTC115E series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT416



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	ø	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT416			SC-75		04-11-04 06-03-16

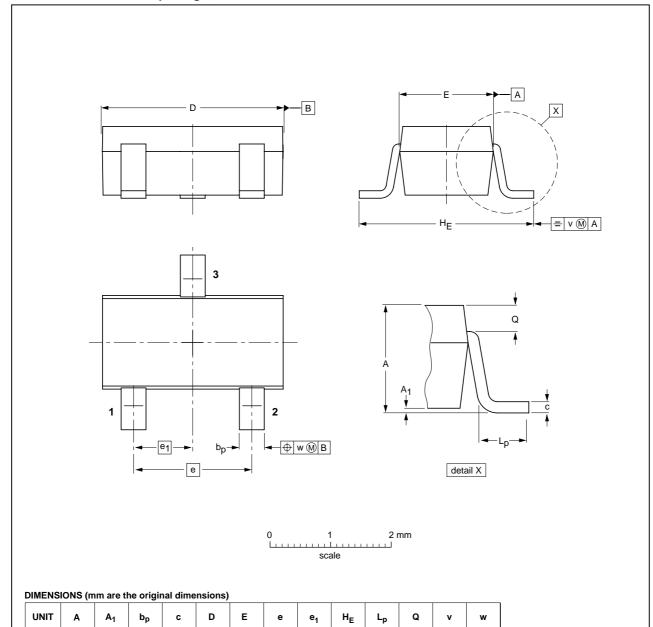
2004 Aug 06 6

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

Plastic surface-mounted package; 3 leads

SOT346



OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT346		TO-236	SC-59A		-04-11-11 06-03-16

1.9

0.6

0.33

0.2

0.2

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1.3

1.0

0.1

0.013

0.50

0.35

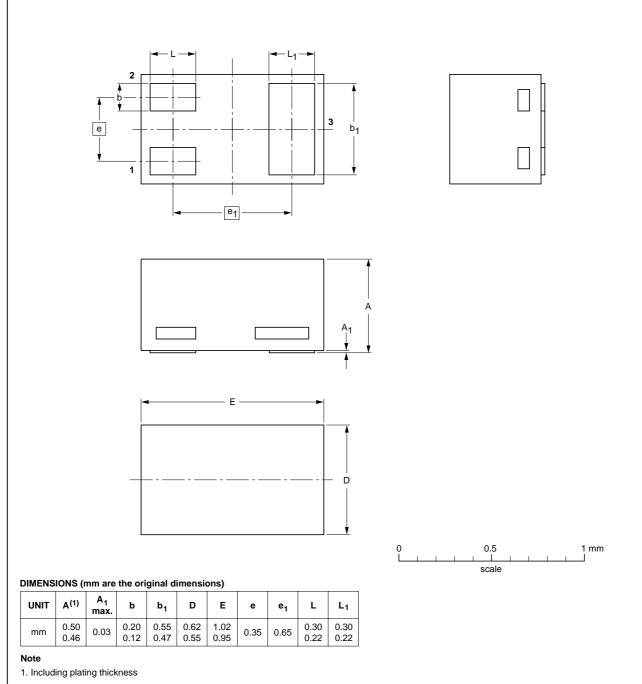
0.26

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



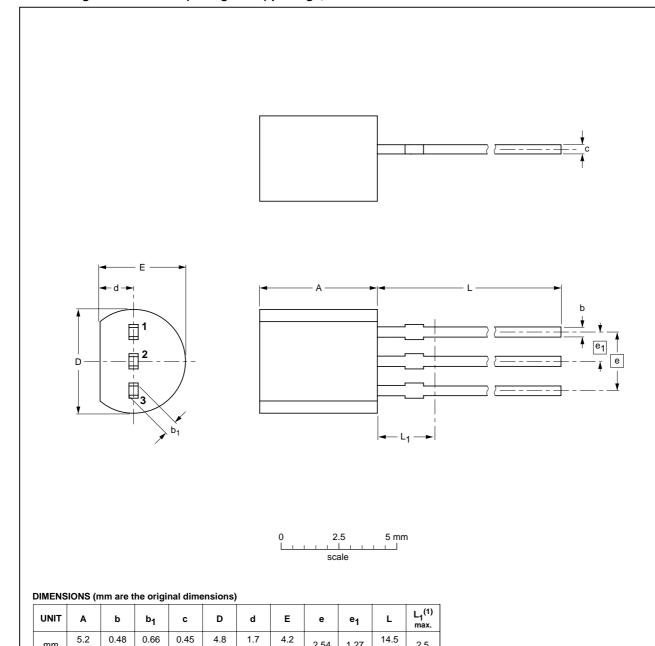
OUTLINE VERSION		REFER	ENCES	EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA	PROJECTION	1SSUE DATE
SOT883			SC-101		03-02-05 03-04-03

NPN resistor-equipped transistors; $R1 = 100 \text{ k}\Omega$, $R2 = 100 \text{ k}\Omega$

PDTC115E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



mm

5.0

0.40

0.55

0.38

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

1.4

4.4

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A		-04-06-28- 04-11-16

1.27

2.5

12.7

2.54

3.6

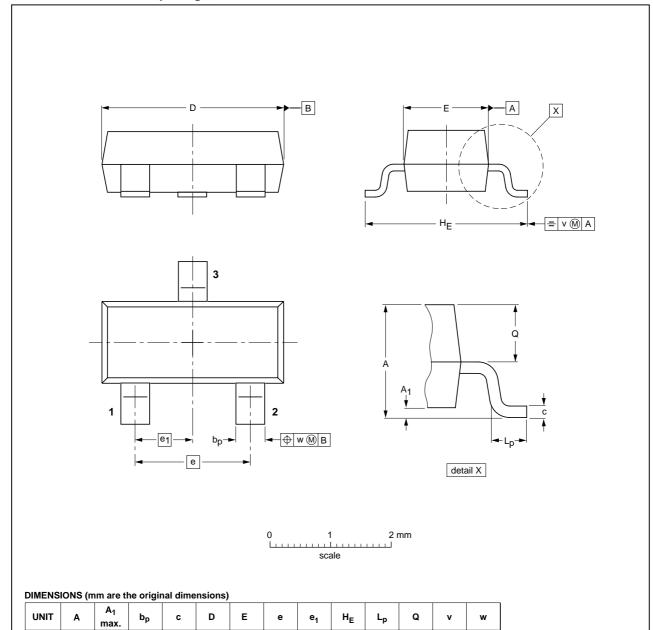
2004 Aug 06 9

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				04-11-04

1.9

0.45

0.55

0.2

0.1

0.48

0.38

0.15

1.1

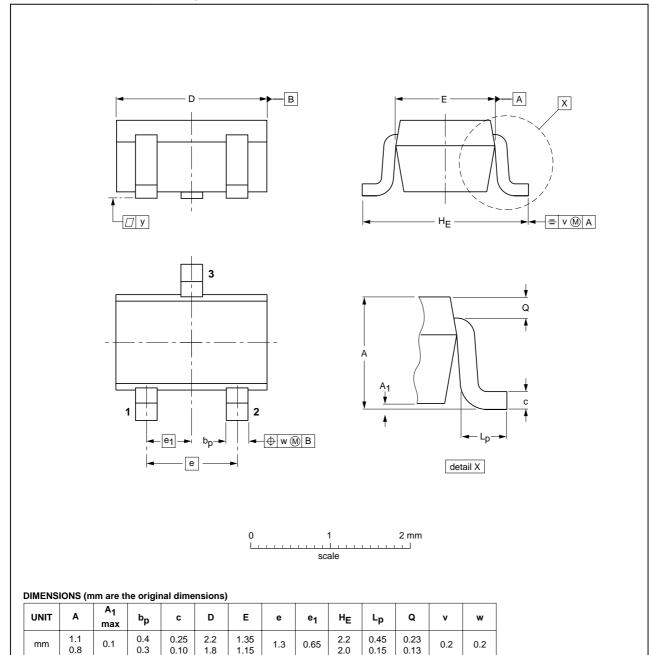
0.9

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

Plastic surface-mounted package; 3 leads

SOT323



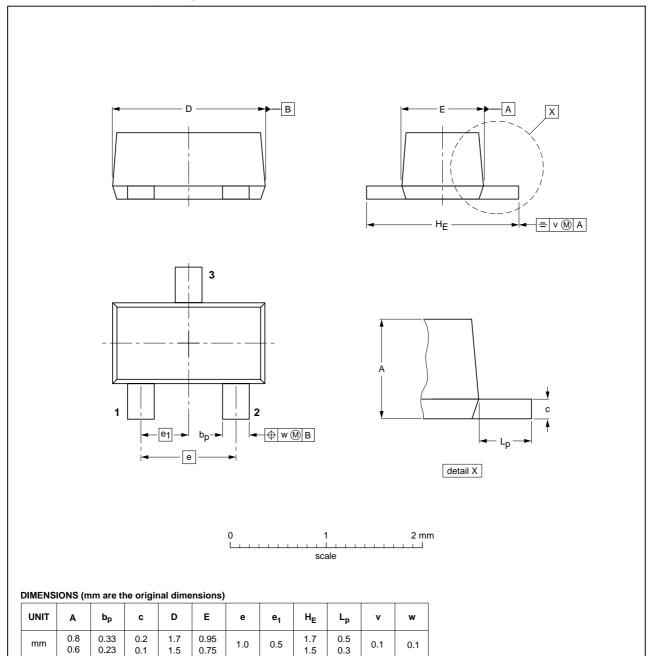
	OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
		IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	SOT323			SC-70			-04-11-04

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

Plastic surface-mounted package; 3 leads

SOT490



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT490			SC-89			05-07-28 06-03-16

NPN resistor-equipped transistors; R1 = 100 k Ω , R2 = 100 k Ω

PDTC115E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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